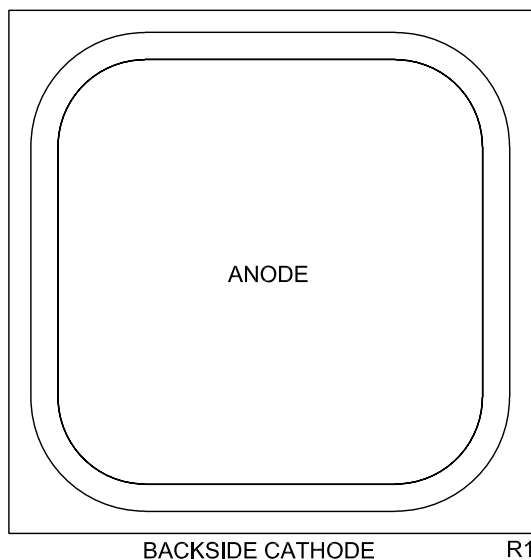


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	32 x 32 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	26 x 26 MILS
Top Side Metalization	Al - 20,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

10,915

PRINCIPAL DEVICE TYPES

CMLSH1-40

1N5817

1N5818

1N5819

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centrasemi.com

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